

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

Kousuke SUZUKI, et al.

Serial Number: 09/045,118

Filed: March 20, 1998

For: **SEMICONDUCTOR DEVICE HAVING AN INSULATION FILM WITH REDUCED WATER CONTENT (AS AMENDED)**



Group Art Unit: 2823

Examiner: N. Berezny

*Amdt*  
*#19 Response*  
*marsha*  
*3/1/01*

AMENDMENT

Director of Patents and Trademarks  
Washington, D.C. 20231

February 14, 2001

Sir:

This is in response to the Office Action dated January 3, 2001. Pursuant to the telephonic Examiner's Interview on February 5, 2001, the statutory six-month period for response ends on February 15, 2001, with a five month Extension of Time (enclosed under separate cover herewith) calculated from the August 15, 2001 Office Action. According to the Examiner, the January 3, 2001 Office Action did not set a new period for response. The following amendments and remarks are respectfully submitted.

A FULLY RESPONSIVE REPLY

The Office Action dated January 3, 2001 indicated that Amendment B filed June 7, 2000 and Amendment C filed October 12, 2000 were not entered. Accordingly, the present Amendment supercedes prior Amendments B and C. It is submitted that the present Amendment is fully responsive to Office Actions dated January 3, 2001, August 15, 2000, and February 14, 2000.

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**IN THE DRAWINGS:**

Enclosed and filed herewith as a separate document and with drawing prints attached, as required by Patent Office practice, is a Request for the Examiner's approval of drawing corrections for Figs. 3, 4, and 16 O.

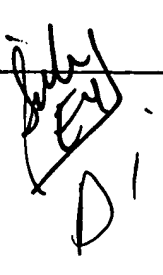
**IN THE TITLE:**

Please delete the title as filed and replace it with the following new title:

--SEMICONDUCTOR DEVICE HAVING AN INSULATION FILM WITH REDUCED WATER  
CONTENT--.

**IN THE SPECIFICATION:**

Please replace the paragraph beginning at page 16, line 27, with the following rewritten  
paragraph:

 --FIG. 9 shows a differential in which the result of FIG. 3 is subtracted from the result of FIG. 4. As already explained with reference to FIG. 4, the SO<sub>2</sub> film deposited under the plasma power of 2000W contains a large amount of H<sub>2</sub>O and OH.--

Please replace the paragraph beginning at page 17, line 2, with the following rewritten paragraph:

P2  
--Further, FIG. 11 shows a differential in which the result of FIG. 3 is subtracted from the result of FIG. 6 in which the high-frequency power is set to 50W. As can be seen clearly from FIG. 11, the amount of H<sub>2</sub>O and OH released from the SiO<sub>2</sub> film is deposited under the high-frequency power of 50W is reduced further as compared with the case of FIG. 10.--

Please replace the paragraph beginning at page 17, line 9, with the following rewritten paragraph:

Sub  
ES  
P3  
~~--Further, FIG. 12 shows a differential in which the result of FIG. 3 is subtracted from the result of FIG. 7 in which the deposited SiO<sub>2</sub> film has a refractive index of 1.5. In this case, the amount of release of H<sub>2</sub>O and OH is reduced further. In contrast, FIG. 13 shows the case in which the result of FIG. 3 is subtracted from the result of FIG. 9 in which the deposited SiO<sub>2</sub> film has a refractive index of 1.63. In this case, the amount of H<sub>2</sub>O and OH incorporated into the SiO<sub>2</sub> film starts to increase again.--~~